

Features

- $V_{DS} = 60V, I_D = 30A$
 $R_{DS(ON)} < 33m\Omega @ V_{GS} = 10V$

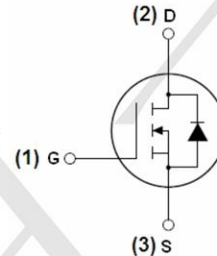
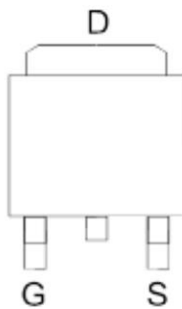
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration

(TO-252-3L)

Top View



Marking:



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 30 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 20 | A |
| Pulsed Drain Current | I_{DM} | 74 | A |
| Maximum Power Dissipation | P_D | 50 | W |
| Derating factor | | 0.33 | W/ $^\circ C$ |
| Single pulse avalanche energy ^(Note 5) | E_{AS} | 144 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--|-----------------|---|--------------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 3 | $^\circ C/W$ |
|--|-----------------|---|--------------|

Electrical Characteristics (T_A=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|--|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 60 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1.4 | 1.8 | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =20A | - | 26 | 33 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =5V, I _D =20A | - | 30 | - | S |
| Dynamic Characteristics (Note 4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =30V, V _{GS} =0V, F=1.0MHz | - | 1900 | - | PF |
| Output Capacitance | C _{oss} | | - | 130 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 95 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DS} =30V, R _L =1.5Ω V _{GS} =10V, R _G =3Ω | - | 5 | - | nS |
| Turn-on Rise Time | t _r | | - | 2.6 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 16.1 | - | nS |
| Turn-Off Fall Time | t _f | | - | 2.3 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =30V, I _D =20A, V _{GS} =10V | - | 30 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 4.5 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 7.5 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V, I _S =30A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | I _S | | - | - | 30 | A |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F =20A di/dt = 100A/μs (Note3) | - | 35 | - | nS |
| Reverse Recovery Charge | Q _{rr} | | - | 53 | - | nC |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

Typical Characteristics

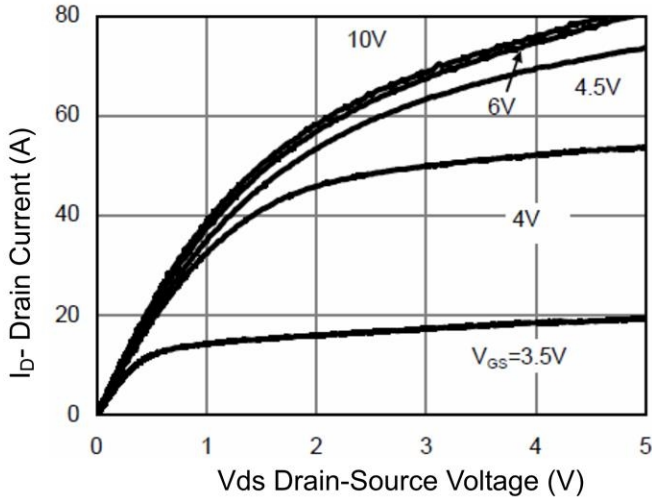


Figure 1 Output Characteristics

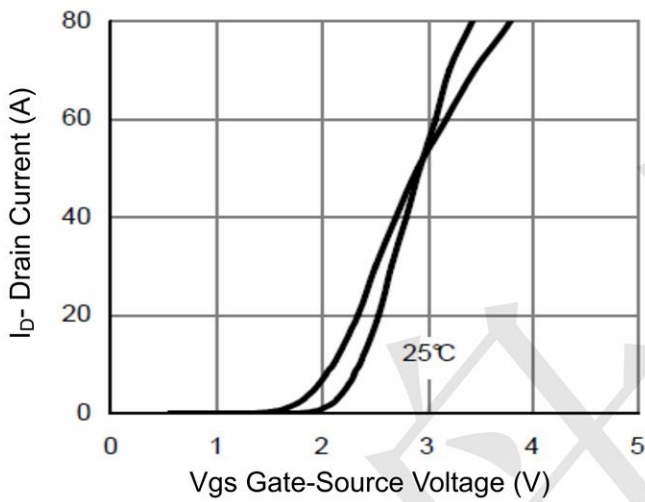


Figure 2 Transfer Characteristics

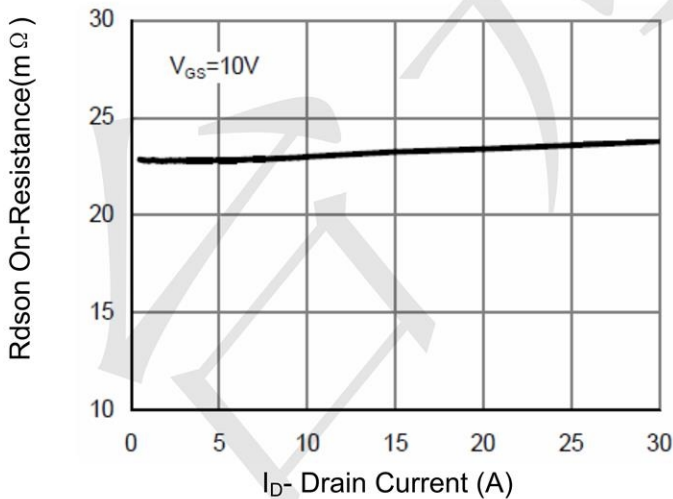


Figure 3 Rds(on)- Drain Current

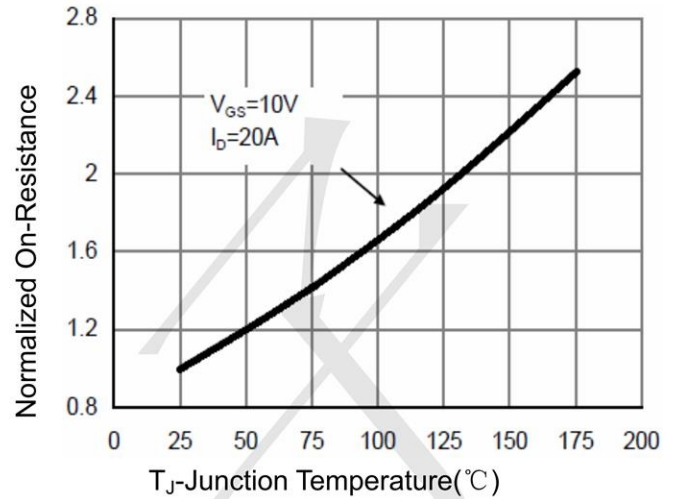


Figure 4 Rds(on)-Junction Temperature

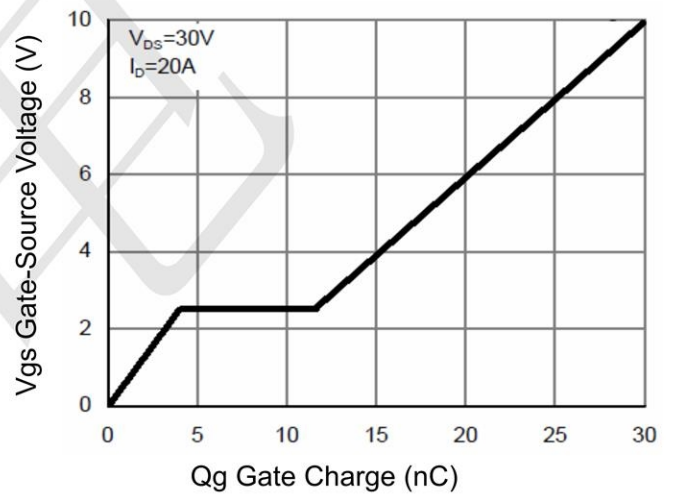


Figure 5 Gate Charge

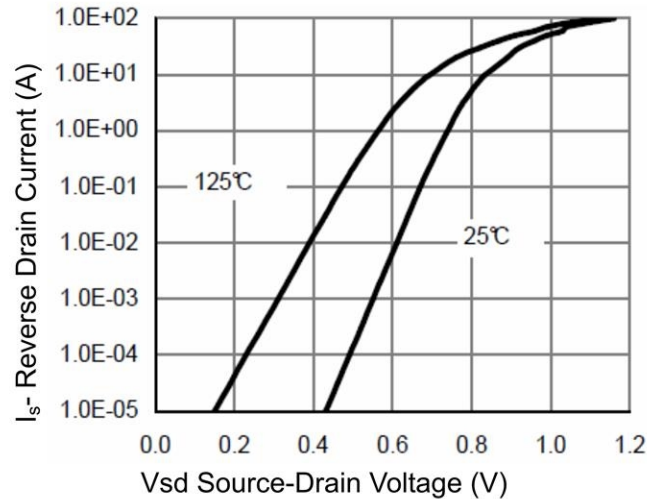


Figure 6 Source- Drain Diode Forward

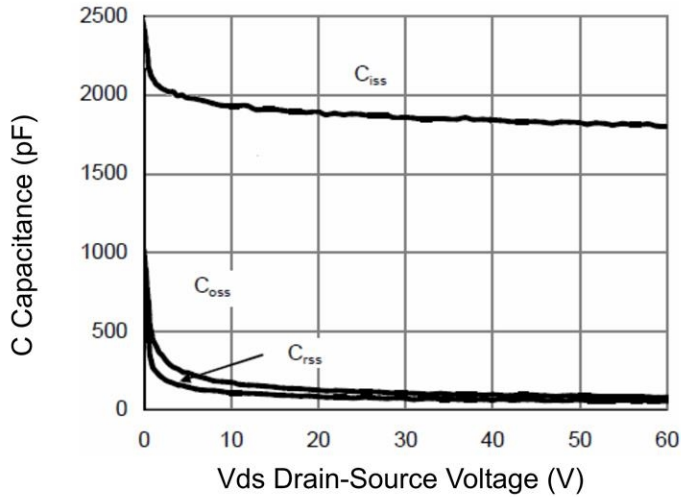


Figure 7 Capacitance vs Vds

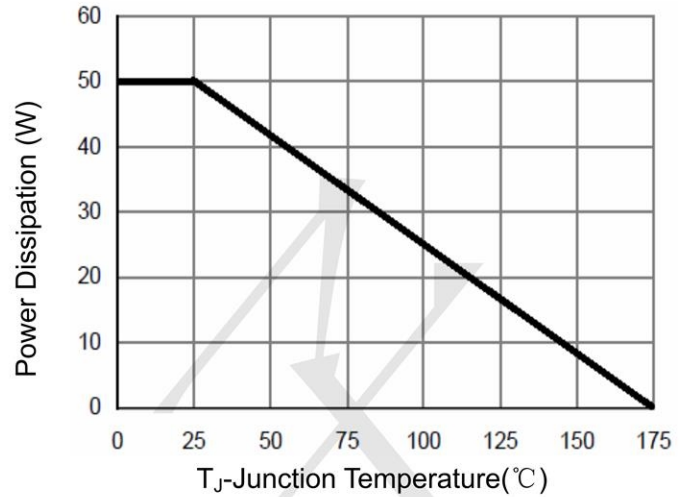


Figure 9 Power De-rating

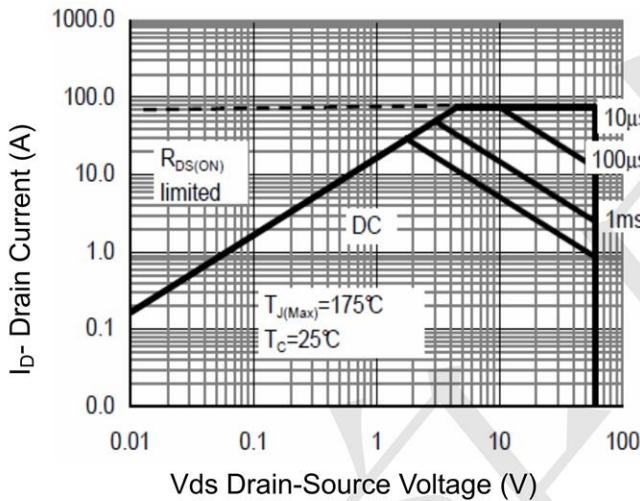


Figure 8 Safe Operation Area

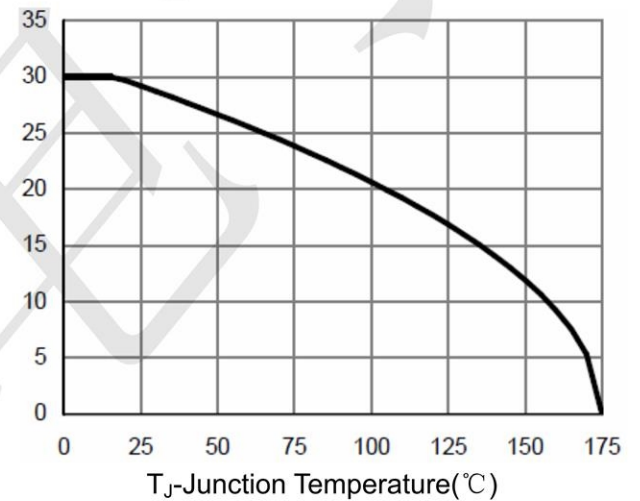


Figure 10 $V_{GS(th)}$ vs Junction Temperature

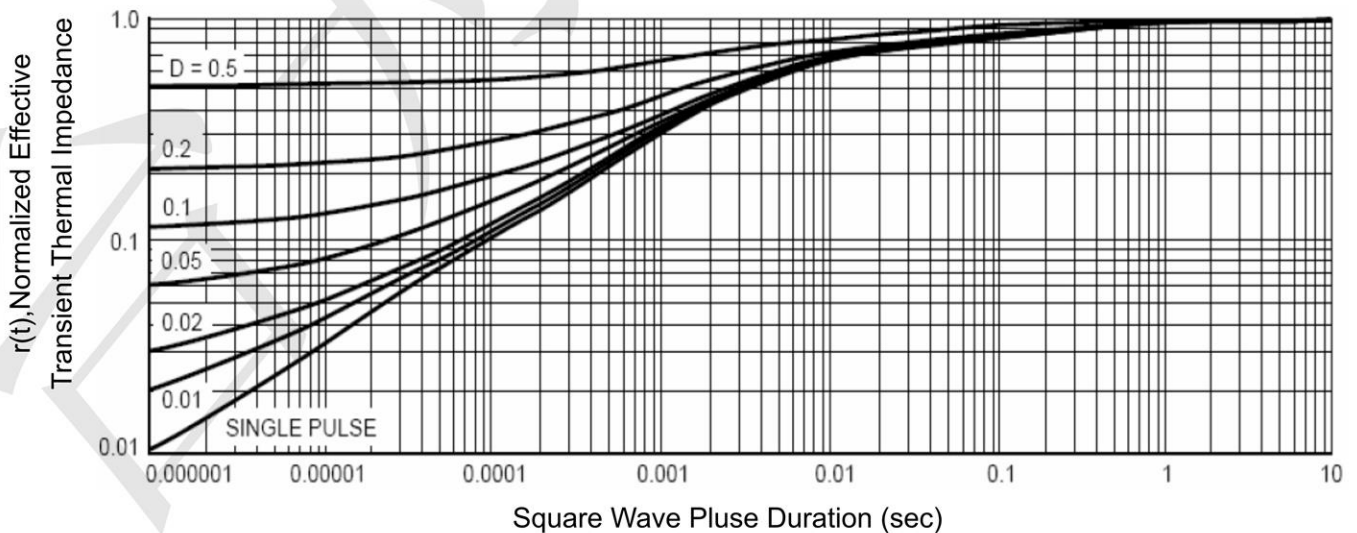
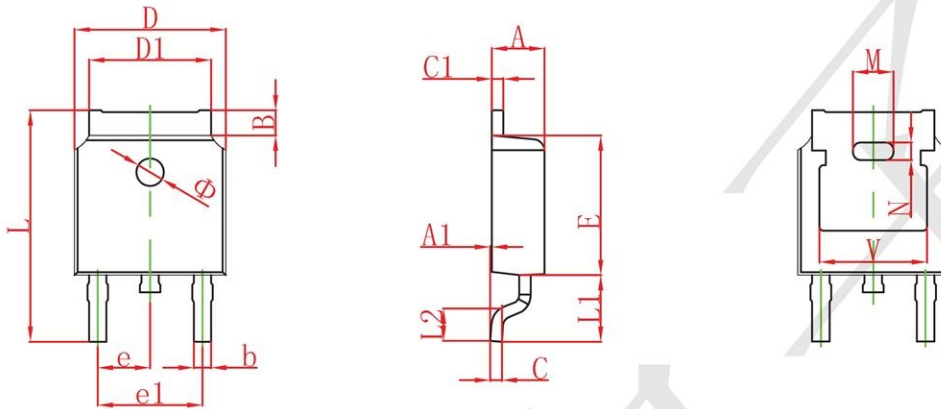


Figure 11 Normalized Maximum Transient Thermal Impedance

TO252 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.200 | 2.380 | 0.087 | 0.094 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| B | 0.800 | 1.400 | 0.031 | 0.055 |
| b | 0.710 | 0.810 | 0.028 | 0.032 |
| c | 0.460 | 0.560 | 0.018 | 0.022 |
| c1 | 0.460 | 0.560 | 0.018 | 0.022 |
| D | 6.500 | 6.700 | 0.256 | 0.264 |
| D1 | 5.130 | 5.460 | 0.202 | 0.215 |
| E | 6.000 | 6.200 | 0.236 | 0.244 |
| e | 2.286 TYP. | | 0.090 TYP. | |
| e1 | 4.327 | 4.727 | 0.170 | 0.186 |
| M | 1.778REF. | | 0.070REF. | |
| N | 0.762REF. | | 0.018REF. | |
| L | 9.800 | 10.400 | 0.386 | 0.409 |
| L1 | 2.9REF. | | 0.114REF. | |
| L2 | 1.400 | 1.700 | 0.055 | 0.067 |
| V | 4.830 REF. | | 0.190 REF. | |
| Φ | 1.100 | 1.300 | 0.043 | 0.051 |

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